Title (en)
METHOD AND DEVICE FOR TREATING A WAFER

Title (de)
VERFAHREN UND VORRICHTUNG ZUR BEHANDLUNG EINES WAFERS

Title (fr)
PROCÉDÉ ET DISPOSITIF DE TRAITEMENT D'UNE PLAQUETTE

Publication
EP 2430664 A2 20120321 (DE)

Application
EP 10720400 A 20100512

Priority
• EP 2010056555 W 20100512
• DE 102009022337 A 20090513

Abstract (en)
[origin: CA2761459A1] In a method for coating a wafer to produce solar cells, a metal such as nickel, copper, or silver is deposited on the wafer in a continuous process in a coating bath containing said metal. A wafer is inserted into the coating bath, and at a time at which a first area of the wafer already extends into the coating bath but a second area does not yet extend into the coating bath, a current surge is applied to the second area of the wafer to initiate the galvanic deposition of the metal on the first area of the wafer reaching into the coating bath for a subsequent further automatic coating, with the wafer completely inserted into the coating bath, also of the remaining area of the wafer without further current surge or current flow.

IPC 8 full level
H01L 31/0224 (2006.01)

CPC (source: EP KR US)
C25D 5/02 (2013.01 - KR); **C25D 5/024** (2013.01 - EP US); **C25D 7/123** (2013.01 - EP US); **C25D 17/001** (2013.01 - EP US); **C25D 17/005** (2013.01 - EP US); **H01L 31/022425** (2013.01 - EP US); **H01L 31/04** (2013.01 - KR); **H01L 31/18** (2013.01 - EP KR US); **Y02E 10/50** (2013.01 - EP US)

Citation (search report)
See references of WO 2010130786A2

Citation (examination)
JP 2007131940 A 20070531 - HITACHI CHEMICAL CO LTD

Cited by
CN110528041A

Designated contracting state (EPC)
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO SE SI SK SM TR

DOCDB simple family (publication)
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DE 102009022337 A 20090513; AU 2010247404 A 20100512; CA 2761459 A 20100512; CN 201080020789 A 20100512; EP 10720400 A 20100512; EP 2010056555 W 20100512; IL 21630911 A 20111110; JP 2012510292 A 20100512; KR 20117026951 A 20100512; MX 2011011985 A 20100512; SG 2011078755 A 20100512; TW 99115342 A 20100513; US 201113294569 A 20111111